Transistors

# 4V Drive Nch MOSFET **RSQ045N03**

## Structure

Silicon N-channel MOSFET

## Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT6).
- 3) Low voltage drive (4V drive).

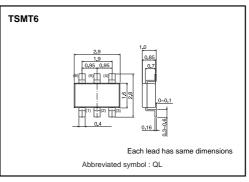
## Applications

Switching

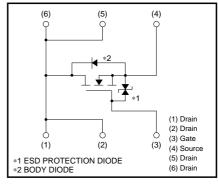
#### Packaging specifications

	Package	Taping	
Туре	Code	TR	
	Basic ordering unit (pieces)	3000	
RSQ045N03		0	

## •Dimensions (Unit : mm)



#### Inner circuit



#### Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	20	V	
Droin ourrant	Continuous	ID	±4.5	А	
Drain current	Pulsed	I <sub>DP</sub> *1	±18	А	
Source current	Continuous	ls	1.0	А	
(Body diode)	Pulsed	I <sub>SP</sub> *1	18	А	
Total power dissipation		P <sub>D</sub> *2	1.25	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1% \*2 Mounted on a ceramic board

### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	100	°C/W

\* Mounted on a ceramic board



## Transistors

### •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	10	μA	Vgs=20V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V	
Zero gate voltage drain current	IDSS	-	-	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V	
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	
Static drain-source on-state resistance		-	27	38	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 10V	
	$R_{DS(on)^*}$	-	36	51	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 4.5V	
		-	40	56	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 4V	
Forward transfer admittance	Y <sub>fs</sub> *	3.5	-	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A	
Input capacitance	Ciss	-	520	_	pF	V <sub>DS</sub> = 10V	
Output capacitance	Coss	-	150	-	рF	Vgs=0V	
Reverse transfer capacitance	Crss	-	95	-	рF	f=1MHz	
Turn-on delay time	td (on) *	-	12	-	ns	Vdd≒ 15V	
Rise time	tr *	-	19	-	ns	ID= 2.25A	
Turn-off delay time	td (off) *	-	41	_	ns	Vgs= 10V R∟=6.67Ω	
Fall time	t <sub>f</sub> *	-	14	_	ns	$R_{G}=10\Omega$	
Total gate charge	Qg *	-	6.8	9.5	nC	V <sub>DD</sub> ≒15V V <sub>GS</sub> =5V	
Gate-source charge	Q <sub>gs</sub> *	-	1.6	-	nC	ID= 4.5A	
Gate-drain charge	Q <sub>gd</sub> *	-	2.3	_	nC	R∟=3.33Ω Rg=10Ω	

## ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	1.2	V	I <sub>S</sub> = 1.0A, V <sub>GS</sub> =0V

### •Electrical characteristic curves

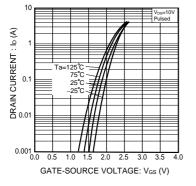


Fig.1 Typical Transfer Characteristics

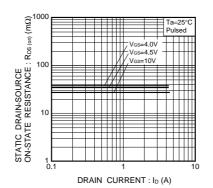


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (I)

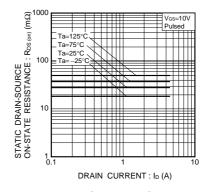
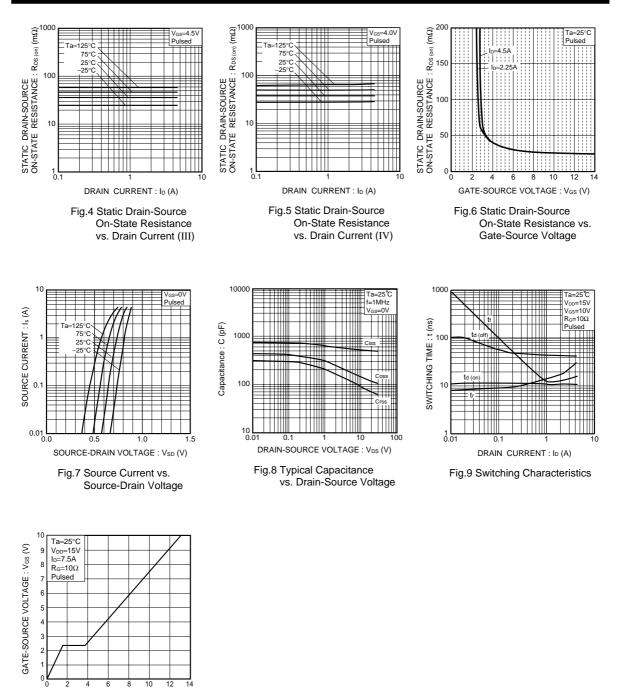


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (II)

# RSQ045N03

## Transistors



TOTAL GATE CHARGE : Qg (nC) Fig.10 Dynamic Input Characteristics

ROHM

## Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the
  product described in this document are for reference only. Upon actual use, therefore, please request
  that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or
  otherwise dispose of the same, no express or implied right or license to practice or commercially
  exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

It is our top priority to supply products with the utmost quality and reliability. However, there is always a chance of failure due to unexpected factors. Therefore, please take into account the derating characteristics and allow for sufficient safety features, such as extra margin, anti-flammability, and fail-safe measures when designing in order to prevent possible accidents that may result in bodily harm or fire caused by component failure. ROHM cannot be held responsible for any damages arising from the use of the products under conditions out of the range of the specifications or due to non-compliance with the NOTES specified in this catalog.

Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact your nearest sales office.

# **ROHM** Customer Support System

THE AMERICAS / EUROPE / ASIA / JAPAN

## www.rohm.com

Contact us : webmaster@rohm.co.jp

Copyright © 2007 ROHM CO.,LTD. ROHM CO., LTD. 21, Saiin Mizosaki-cho, Ukyo-ku, Kyoto 615-8585, Japan TEL : +81-75-311-2121 FAX : +81-75-315-0172

Appendix1-Rev2.0

ROHM